

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	etching near RIE near primary near mask near pattern near overcoat near layer near DRIE	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/22 08:23
L2	1154	438/712	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/22 08:24
S1	1	10/675203	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 11:36
S2	323243	((silicon adj dioxide) or (SiO2 or SiOx or SiOn or "SiO.sub2" or "SiO. subx" or "SiO.subn" or "SiO.sub.2" or "SiO.sub.x" or "SiO.sub.n"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/13 09:12
S3	364844	(aluminum adj oxide) or (alumina OR AlO3 or AlO3 or AlOn or "AlO. sub3" or "AlO.subx" or "AlO.subn" or "AlO.sub.3" or "AlO.sub.x" or "AlO. sub.n")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/11 17:06
S4	801195	Cu or Nife or Ni-fe or Sc-Zn or Sczn	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 08:22
S5	1783805	etch or remove	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 08:24
S6	41700	RIE or (reactive adj ion adj etch)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 08:24
S7	30201	DRIE or (deep adj reactive adj ion adj etch)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 08:24

## EAST Search History

S8	1817901	S5 or S6 or S7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 08:25
S9	590	S5 and S6 and S7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 08:25
S10	75590	S2 and S3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 08:25
S11	40337	S3 and S4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 08:25
S12	15132	S10 and S11	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 08:26
S13	69	S9 and S10	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 08:26
S14	19	S9 and S11	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 08:26
S15	16	S9 and S12	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 08:45
S16	2125253	(dic\$3 or cut\$3 or slic\$3 or saw\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 08:30
S17	539722	S16 and (S2 or (silicon or Si) or (silicon adj substrate) or (silicon adj wafer) or (silicon adj thin sdj head))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 08:32

## EAST Search History

S18	289	S17 and S9	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 08:34
S19	9	S18 and S12	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 08:34
S20	572	438/712.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 08:45
S21	103	S20 and S16	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 09:03
S22	50	seperat\$4 and die and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 09:07
S23	0	seperat\$4 near (wafer or die) and DRIE	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 09:08
S24	0	DRIE and seperat\$4 near (wafer or die)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 09:09
S25	10	seperat\$4 near (wafer or die)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 09:09
S26	3606	slic\$4 near (die or wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 09:10
S27	43149	cut\$4 near (die or wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 09:10

## EAST Search History

S28	46130	S27 or S26	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 09:11
S29	587	S28 and RIE	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 09:11
S30	574	S28 and DRIE	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 09:16
S31	23	throughhole and DRIE	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 09:18
S32	1908	(through adj hole) and DRIE	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 09:19
S33	326	throughhole and etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 09:19
S34	11080	(through adj hole) and etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 09:19
S35	1988821	S34 and silicon substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 09:20
S36	2608	S34 and (silicon adj substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 09:20
S37	158	S36 and S7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 09:26

## EAST Search History

S38	5	DRIE near silicon near substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/21 09:36
S39	11	DRIE near substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/21 10:08
S40	0	DRIE near resist near ((aluminum adj oxide) or (alumina OR AlO3 or AlO3 or AlOn or "AlO.sub3" or "AlO. subx" or "AlO.subn" or "AlO.sub.3" or "AlO.sub.x" or "AlO.sub.n"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/21 10:08
S41	0	DRIE near ((aluminum adj oxide) or (alumina OR AlO3 or AlO3 or AlOn or "AlO.sub3" or "AlO.subx" or "AlO. subn" or "AlO.sub.3" or "AlO.sub.x" or "AlO.sub.n"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/21 10:09
S42	130	DRIE and ((aluminum adj oxide) or (alumina OR AlO3 or AlO3 or AlOn or "AlO.sub3" or "AlO.subx" or "AlO. subn" or "AlO.sub.3" or "AlO.sub.x" or "AlO.sub.n"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/21 10:10
S43	112	S42 and etch\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/21 10:40
S44	2	"6897148".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/21 13:58
S45	2	"6184060".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 11:36
S46	0	2002/0218140	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/21 13:59
S47	0	US2002/0218140	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/21 13:59

## EAST Search History

S48	0	US2002-0218140	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/21 13:59
S49	22	"0218140"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/21 14:00
S50	0	"218140" and tamamori	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/21 14:01
S51	0	08/218140 and Tamamori	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/21 14:01
S52	33	"2002" and Tamamori	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/21 14:02
S53	5	laser adj cut adj wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/21 14:09
S54	21	laser adj cut adj (dice or die)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/21 14:09
S55	288975	S54 and (aluminum adj oxide) or (alumina OR AlO3 or AlO3 or AlOn or "AlO.sub3" or "AlO.subx" or "AlO.subn" or "AlO.sub.3" or "AlO.sub.x" or "AlO.sub.n")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/21 14:10
S56	0	S54 and ((aluminum adj oxide) or (alumina OR AlO3 or AlO3 or AlOn or "AlO.sub3" or "AlO.subx" or "AlO.subn" or "AlO.sub.3" or "AlO.sub.x" or "AlO.sub.n"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/21 14:10

## EAST Search History

S57	414	(cut adj (die or dice or wafer)) and ((aluminum adj oxide) or (alumina OR AlO3 or AlO3 or AlOn or "AlO. sub3" or "AlO.subx" or "AlO.subn" or "AlO.sub.3" or "AlO.sub.x" or "AlO. sub.n"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/21 14:13
S58	40	S57 and cut.ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/22 08:20
S59	9	S58 and ((silicon adj dioxide) or (SiO2 or SiOx or SiOn or "SiO.sub2" or "SiO.subx" or "SiO.subn" or "SiO. sub.2" or "SiO.sub.x" or "SiO.sub. n"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/21 14:47
S60	364844	(aluminum adj oxide) or (alumina OR AlO3 or AlO3 or AlOn or "AlO. sub3" or "AlO.subx" or "AlO.subn" or "AlO.sub.3" or "AlO.sub.x" or "AlO. sub.n")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/22 08:20
S61	414	(cut adj (die or dice or wafer)) and ((aluminum adj oxide) or (alumina OR AlO3 or AlO3 or AlOn or "AlO. sub3" or "AlO.subx" or "AlO.subn" or "AlO.sub.3" or "AlO.sub.x" or "AlO. sub.n"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/22 08:20
S62	40	S61 and cut.ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/22 08:20
S63	40	S62 and S60	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/22 08:45
S64	62	thin adj film adj slider\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/22 08:46
S65	33	S64 and cut	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/22 14:16

## EAST Search History

S66	14	S65 and ((silicon adj dioxide) or (SiO2 or SiOx or SiOn or "SiO.sub2" or "SiO.subx" or "SiO.subn" or "SiO.sub.2" or "SiO.sub.x" or "SiO.sub.n"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/22 08:47
S67	3	S66 and ((aluminum adj oxide) or (alumina OR AlO3 or AlO3 or AlOn or "AlO.sub3" or "AlO.subx" or "AlO.subn" or "AlO.sub.3" or "AlO.sub.x" or "AlO.sub.n"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/22 08:47
S68	2	"4624048".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/22 09:27
S69	293	wafer adj packaging	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/22 09:27
S70	5777	(wafer or die or dice) adj packag\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/22 09:28
S71	8	S70 and DRIE	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/22 09:33
S72	2	S71 and cut	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/22 09:28
S73	0	die and seperat\$4 and etch.ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/22 09:34
S74	17090	(die or dice or wafer) and (seperat\$4 or cut\$4) and (etch or (deep near etch) or DRIE or RIE or (reactive near etch))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/22 09:37
S75	8385	S74 and ((silicon adj dioxide) or (SiO2 or SiOx or SiOn or "SiO.sub2" or "SiO.subx" or "SiO.subn" or "SiO.sub.2" or "SiO.sub.x" or "SiO.sub.n"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/22 09:36

## EAST Search History

S76	1756	S75 and ((aluminum adj oxide) or (alumina OR AlO3 or AlO3 or AlOn or "AlO.sub3" or "AlO.subx" or "AlO. subn" or "AlO.sub.3" or "AlO.sub.x" or "AlO.sub.n"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/22 09:37
S77	45	S76 and (seperat\$4 or cut\$4).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/22 13:28
S78	316	RIE and DRIE	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/22 13:28
S79	92	S78 and (Cu or Ti or TiW or NiFe)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/22 13:44
S80	23	S79 and seed	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/22 13:31
S81	9	S80 and ((aluminum adj oxide) or (alumina OR AlO3 or AlO3 or AlOn or "AlO.sub3" or "AlO.subx" or "AlO. subn" or "AlO.sub.3" or "AlO.sub.x" or "AlO.sub.n"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/22 13:31
S82	84	S79 and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/22 13:44
S83	1	"20030218140".PN.	US-PGPUB	OR	ON	2005/06/22 13:59
S84	841	DRIE and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/22 14:16
S85	13946	RIE and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/22 14:16

## EAST Search History

S86	271	S85 and S84	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/22 14:17
S87	193	S86 and ((silicon adj dioxide) or (SiO2 or SiOx or SiOn or "SiO.sub2" or "SiO.subx" or "SiO.subn" or "SiO.sub.2" or "SiO.sub.x" or "SiO.sub.n"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/22 14:24
S88	152	S87 and (hardmask or mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/22 14:31
S89	0	S87 and (hardmask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/22 14:25
S90	0	S87 and (hard adj resist)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/22 14:25
S91	916675	silicon and silicon dioxide and etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/22 14:31
S92	32310	silicon and silicon adj dioxide and etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/22 14:31
S93	139	S92 and S86	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/22 14:32
S94	51318	((silicon adj dioxide) or (SiO2 or SiOx or SiOn or "SiO.sub2" or "SiO.subx" or "SiO.subn" or "SiO.sub.2" or "SiO.sub.x" or "SiO.sub.n")) and etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/22 14:33
S95	580	S94 and DRIE or (deep adj reactive adj ion adj etch)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/22 14:37

## EAST Search History

S96	3	S95 and (DRIE adj mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/22 14:40
S97	212	S95 and (etch adj stop)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/22 14:43
S98	113	S97 and S85	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/22 16:22
S99	178	(dual adj damascene) and (photo adj resist) and (etch adj stop)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/22 16:27
S100	0	S99 and DRIE	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/22 16:24
S101	0	S99 and (deep adj reactive adj ion)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/22 16:24
S102	145	S99 and ((silicon adj dioxide) or (SiO2 or SiOx or SiOn or "SiO.sub2" or "SiO.subx" or "SiO.subn" or "SiO.sub.2" or "SiO.sub.x" or "SiO.sub.n"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/22 16:28
S103	142	S102 and substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/22 16:51
S104	4	S103 and (etch near substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/22 16:46
S105	7	S103 and ((aluminum adj oxide) or (alumina OR AlO3 or AlO3 or AlOn or "AlO.sub3" or "AlO.subx" or "AlO.subn" or "AlO.sub.3" or "AlO.sub.x" or "AlO.sub.n"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/22 16:47

## EAST Search History

S10 6	2	"6477019".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 08:11
S10 7	1	10/172125	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 08:11
S10 8	0	cutting near (magnetic adj head adj devices)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 08:12
S10 9	0	cut near (magnetic adj head adj devices)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 08:12
S11 0	204	(magnetic adj head adj devices)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 08:12
S11 1	404990	S110 and cut wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 08:12
S11 2	2	S110 and cut adj wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 08:18
S11 3	3322	cut adj wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 08:19
S11 4	0	S113 and RIE near cut\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 08:19
S11 5	153	S113 and RIE	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 08:48

## EAST Search History

S11 6	2	09/876888	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 08:48
S11 7	2764	copper and (hard adj mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 10:33
S11 8	14	copper near (hard adj mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 10:36
S11 9	0	10/675203.pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 10:34
S12 0	1	10/675203	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 10:34
S12 1	4	copper adj (hard adj mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 10:37
S12 2	1	08/689559	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 10:37
S12 3	1	08/698559	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 14:36
S12 4	1	10/675203	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/25 07:53
S12 5	4	"6908716".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/25 08:26

## EAST Search History

S12 6	2	"6171945".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/25 09:09
S12 7	2	"6018861".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/25 09:09
S12 8	358396	((silicon adj dioxide) or (SiO2 or SiOx or SiOn or "SiO.sub2" or "SiO. subx" or "SiO.subn" or "SiO.sub.2" or "SiO.sub.x" or "SiO.sub.n"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/11 17:06
S12 9	395117	(aluminum adj oxide) or (alumina OR AlO3 or AlO3 or AlOn or "AlO. sub3" or "AlO.subx" or "AlO.subn" or "AlO.sub.3" or "AlO.sub.x" or "AlO. sub.n")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/11 18:32
S13 0	84641	S128 and S129	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/11 17:06
S13 1	67	DRIE near mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/11 17:06
S13 2	861	RIE near mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/11 17:06
S13 3	168009	silicon near substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/11 17:11
S13 4	8433	S130 and S133	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/11 17:17
S13 5	105	nickle adj (plating or plated)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/11 17:12

## EAST Search History

S13 7	4	nickel near RIE	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/11 17:11
S13 8	2	NiFe near RIE	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/11 17:16
S13 9	453276	nickel or (nickel adj alloy) or Ni2 or Nix or Nin or Nisubx or Nisubn or "Ni.subx" or "Ni.subn" or "Ni.sub.x" or "Ni.sub.n"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/11 17:47
S14 0	47759	RIE or (reactive adj ion adj etch)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/11 17:58
S14 1	4	S139 near S140	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/11 17:16
S14 2	65	NiFe near mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/11 17:31
S14 3	281	S139 near mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/11 17:16
S14 4	346	S142 or S143	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/11 17:16
S14 5	20	S134 and S144	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/11 17:27
S14 6	24	drie near (cut or seperate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/11 17:18

## EAST Search History

S14 7	0	plasma near etch near cut near wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/11 17:27
S14 8	1	etch near cut near wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/11 17:28
S15 0	339400	etch Silicon near substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/11 17:28
S15 1	1055	etch near Silicon near substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/11 17:28
S15 2	41	S151 and S128 and S129	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/11 17:43
S15 3	5	S152 and S139	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/11 17:29
S15 4	11	S144 with S128	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/11 17:31
S15 5	4098	S139 and S129 and S133	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/11 17:43
S15 6	164	S155 and (etch near (substrate or wafer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/11 17:43
S15 7	24	S156 and DRIE	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/11 17:44